

TDS:EMIC

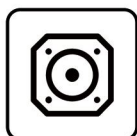
拓 電 半 導 體

自主封測 品質把控 售後保障

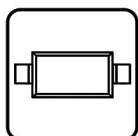
WEB | WWW.TDSEMIC.COM



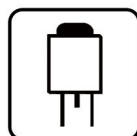
電源管理



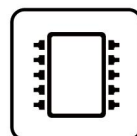
顯示驅動



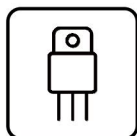
二三極管



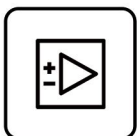
LDO穩壓器



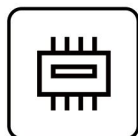
觸摸芯片



MOS管



運算放大器



存儲芯片



MCU



串口通信

SS86C SS86

產品規格說明書

Surface Mount Schottky Rectifier

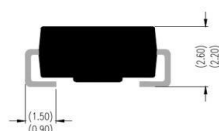
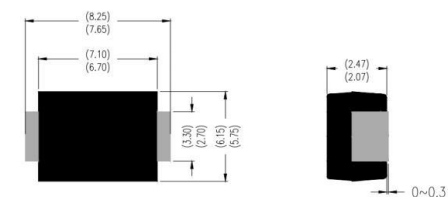
Features

- Guardring for overvoltage protection
- Low power loss
- Extremely fast switching
- High forward surge current capability
- High frequency operation
- Solder dip 260 °C max. 10 s, per JESD 22-B106

Mechanical Data

- Package: DO-214AB (SMC)
- Polarity : Polarity symbol marking on body
- Epoxy: UL 94V-0 rate flame retardant
- Mounting Position : Any

DO-214AB (SMC)



Unit : inch(mm)



Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Unit	SS82C	SS84C	SS86C	SS810C	SS815C	SS820C
Repetitive Peak Reverse Voltage	V _{RRM}	V	20	40	60	100	150	200
Average Rectified Output Current @60Hz sine wave, Resistance load, T _a (FIG.1)	I _O	A	8.0					
Surge(Non-repetitive)Forward Current @60Hz Half-sine wave, 1 cycle, T _a =25 °C	I _{FSM}	A	120					
Storage Temperature	T _{stg}	°C	-55 ~+150					
Junction Temperature	T _j	°C	-55 ~+150			-55 ~+175		

Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Unit	Test Conditions	SS82C	SS84C	SS86C	SS810C	SS815C	SS820C
Maximum instantaneous forward voltage drop per diode	V _F	V	I _{FM} =8.0A	0.55		0.70	0.85	0.95	
Maximum DC reverse current at rated DC blocking voltage per diode	I _R	mA	Ta=25℃	0.2			0.1		
			Ta=100℃	20			5.0		
Typical junction capacitance	Cj	pF	Measured at 1MHz and Applied Reverse Voltage of 4.0 V.D.C.	450		350	270	180	

Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Unit	SS82C	SS84C	SS86C	SS810C	SS815C	SS820C
Thermal Resistance	Between junction and ambient	$R_{\theta JA}$	$^\circ\text{C/W}$	45 ⁽¹⁾					
	Between junction and lead	$R_{\theta JL}$							
				12 ⁽¹⁾					

Note (1)

Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.6" x 0.6" (16 mm x 16 mm) copper pad areas

Characteristics (Typical)

FIG.1: Io-TL Curve

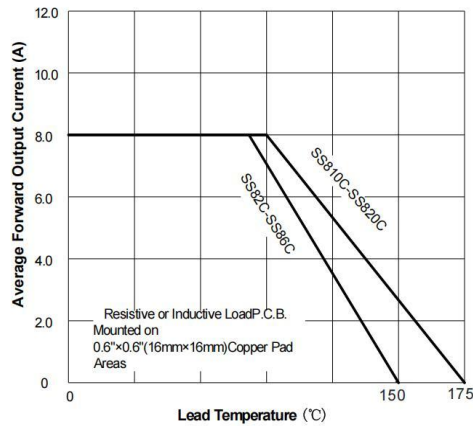


FIG.2: Forward Surge Current Capability

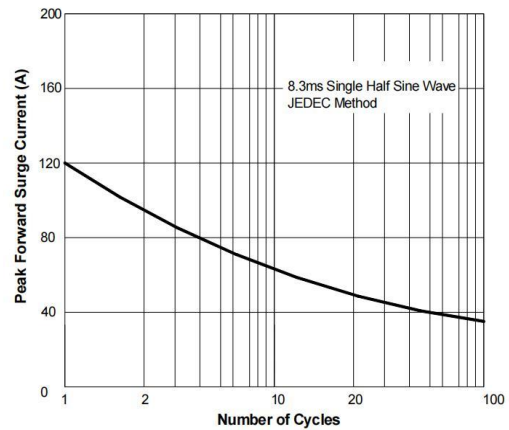


FIG.3: Forward Voltage

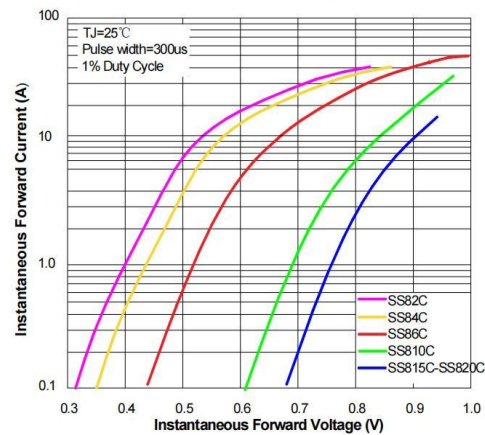


FIG.4: Typical Reverse Characteristics

